

EH3900ETTTS-34.368M TR

Lead Free  COMPLIANT	EU RoHS 2011/65 + 2015/863 COMPLIANT	ChinaRoHS  COMPLIANT	REACH SVHC 163 Jun 15, 2015 COMPLIANT
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ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) LVCMOS (CMOS) 1.8Vdc 4 Pad 3.2mm x 5.0mm Ceramic Surface Mount (SMD) 34.368MHz \pm 100ppm -40°C to +85°C

ELECTRICAL SPECIFICATIONS

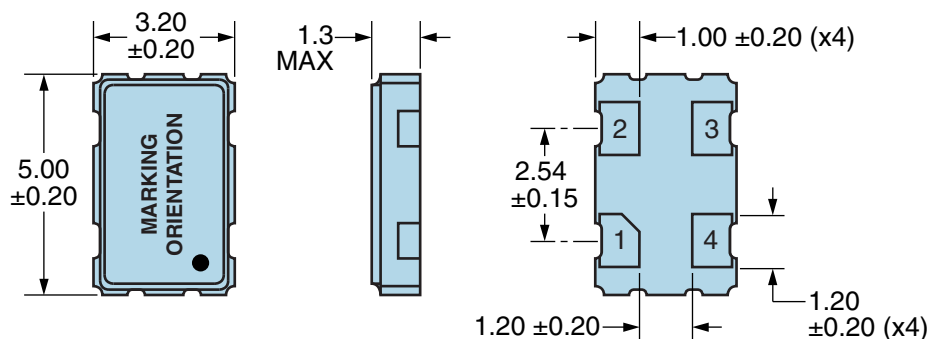
Nominal Frequency	34.368MHz
Frequency Tolerance/Stability	\pm 100ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, 260°C Reflow, Shock, and Vibration)
Aging at 25°C	\pm 5ppm/Year Maximum
Operating Temperature Range	-40°C to +85°C
Supply Voltage	1.8Vdc \pm 5%
Input Current	4mA Maximum (No Load)
Output Voltage Logic High (Voh)	90% of Vdd Minimum (IOH = -8mA)
Output Voltage Logic Low (Vol)	10% of Vdd Maximum (IOL = +8mA)
Rise/Fall Time	6nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50 \pm 5(%) (Measured at 50% of waveform)
Load Drive Capability	15pF Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)
Standby Current	10 μ A Maximum (Pin 1 = Ground)
RMS Phase Jitter	20pSec Typical, 30pSec Maximum (Fj = 12kHz to 20MHz)
Period Jitter (RMS)	15pSec Typical
Period Jitter (pk-pk)	100pSec Typical, 200pSec Maximum
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-883, Method 2002, Condition B
Moisture Resistance	MIL-STD-883, Method 1004
Moisture Sensitivity	J-STD-020, MSL 1
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

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MECHANICAL DIMENSIONS (all dimensions in millimeters)

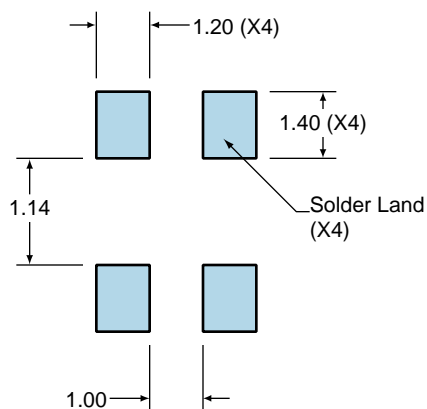


PIN	CONNECTION
1	Tri-State
2	Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	E34.368 E=Ecliptek Designator
2	XXXXX XXXXX=Ecliptek Manufacturing Identifier

Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ± 0.1

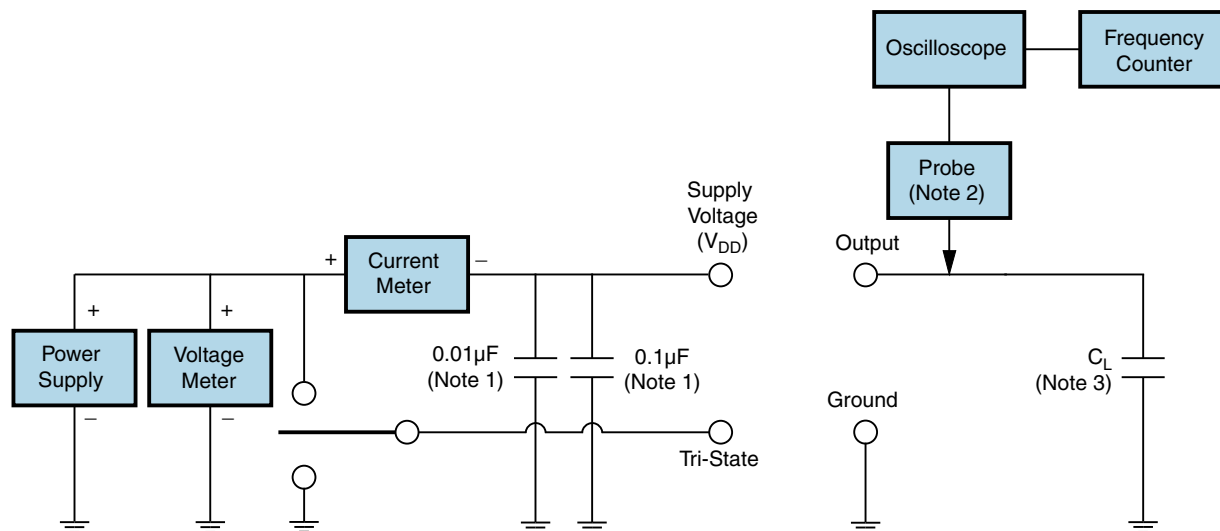
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OUTPUT WAVEFORM & TIMING DIAGRAM



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Test Circuit for CMOS Output



Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

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Tape & Reel Dimensions

Quantity Per Reel: 1,000 units

All Dimensions in Millimeters

Compliant to EIA-481

